

AMENDMENTS TO THE CLAIMS

Applicant submits below a complete listing of the current claims, including marked-up claims with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing. This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for controlling an SCR-type switch, comprising applying to a switch gate several periods of an unrectified high~~[[-]]~~frequency voltage, a power of one ~~[[HF]]~~ high frequency halfwave being insufficient to start the SCR-type switch.
2. (Currently Amended) The control method of claim 1, wherein the ~~[[HF]]~~ high frequency voltage oscillates at a selected frequency between 10 kHz and a few GHz.
3. (Currently Amended) The method of claim 1, wherein the high frequency voltage is applied via an insulating layer formed above a ~~sensitive~~ starting area of the component.
4. (Currently Amended) The method of claim 3, wherein the high frequency voltage is applied above a gate region of a thyristor.
5. (Currently Amended) The method of claim 3, wherein the high frequency voltage is applied above a gate region of a triac.
6. (Currently Amended) The method of claim 3, wherein the high frequency voltage is applied via a high-frequency line having terminals for connection to the high frequency voltage.
7. (Currently Amended) The method of claim 3, wherein the high frequency voltage is applied via a winding that generates a magnetic field or responds to a magnetic field.
8. (Currently Amended) An SCR-type switch component, comprising two main

electrodes and at least one control electrode formed on an insulating layer and arranged above a starting region of the component, said control electrode ~~being intended to be connected~~ controlling the SCR-type switch component in response to an unrectified [[HF]] high frequency power supply.

9. (Currently Amended) The ~~method~~ SCR-type switch component of claim 8, wherein the control electrode is arranged above a gate region of a thyristor.

10. (Previously Presented) The ~~method~~ SCR-type switch component of claim 8, wherein the control electrode is arranged above a gate region of a triac.

11. (Previously Presented) The ~~method~~ SCR-type switch component of claim 8, wherein the control electrode is a high-frequency line having terminals for connection to the high frequency power supply.

12. (Previously Presented) The ~~method~~ SCR-type switch component of claim 8, wherein the high frequency is applied via a winding that generates a magnetic field or responds to a magnetic field.